

NGTB45N60SWG

IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for half bridge resonant applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Low Gate Charge
- Soft, Fast Free Wheeling Diode
- These are Pb-Free Devices

Typical Applications

- Inductive Heating
- Soft Switching

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	600	V
Collector current @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$	I_c	90 45	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	180	A
Diode forward current @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$	I_F	90 45	A
Diode pulsed current, T_{pulse} limited by T_{Jmax}	I_{FM}	180	A
Gate-emitter voltage	V_{GE}	± 20	V
Power Dissipation @ $T_c = 25^\circ\text{C}$ @ $T_c = 100^\circ\text{C}$	P_D	250 50	W
Operating junction temperature range	T_J	-55 to +150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



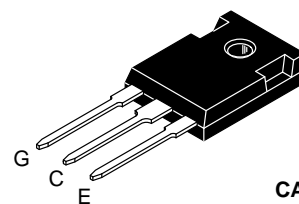
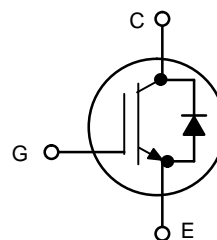
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45 A, 600 V

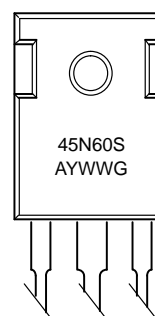
$V_{CEsat} = 2.2 \text{ V}$

$E_{off} = 0.55 \text{ mJ}$



**TO-247
CASE 340AL**

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB45N60SWG	TO-247 (Pb-Free)	30 Units / Rail

NGTB45N60SWG

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.87	°C/W
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	1.47	°C/W
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	600	–	–	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 45\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 45\text{ A}, T_J = 150^\circ\text{C}$	V_{CEsat}	–	2.2 2.6	2.4 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 150\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 150^\circ\text{C}$	I_{CES}	–	–	0.2 2	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	–	–	100	nA

DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	3100	–	pF
Output capacitance		C_{oes}	–	120	–	
Reverse transfer capacitance		C_{res}	–	80	–	
Gate charge total	$V_{CE} = 480\text{ V}, I_C = 45\text{ A}, V_{GE} = 15\text{ V}$	Q_g		134		nC
Gate to emitter charge		Q_{ge}		27		
Gate to collector charge		Q_{gc}		67		

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 45\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$		70		ns
Rise time		t_r		34		
Turn-off delay time		$t_{d(off)}$		144		
Fall time		t_f		68		
Turn-off switching loss		E_{off}		0.55		
Turn-on delay time	$T_J = 150^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 45\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$		70		ns
Rise time		t_r		39		
Turn-off delay time		$t_{d(off)}$		151		
Fall time		t_f		88		
Turn-off switching loss		E_{off}		0.89		

DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 20\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 20\text{ A}, T_J = 150^\circ\text{C}$	V_F		1.1 1.03	1.4	V
Reverse recovery time	$T_J = 25^\circ\text{C}$ $I_F = 25\text{ A}, V_R = 200\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	t_{rr}		376		ns
Reverse recovery charge		Q_{rr}		4145		nc
Reverse recovery current		I_{rrm}		22		A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

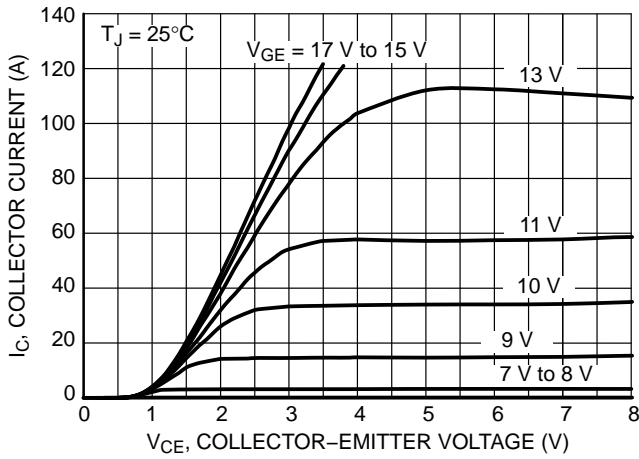


Figure 1. Output Characteristics

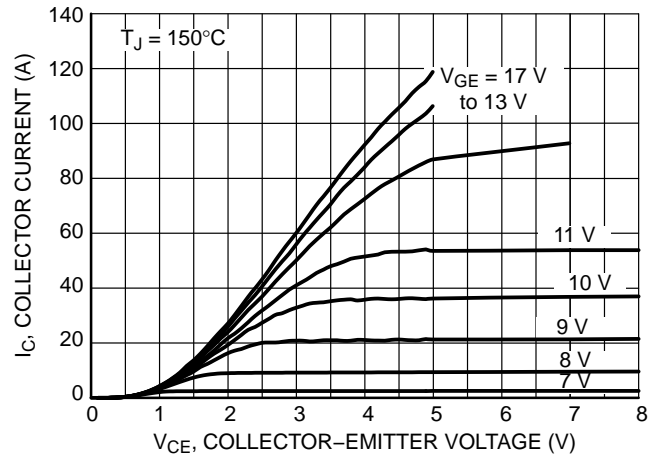


Figure 2. Output Characteristics

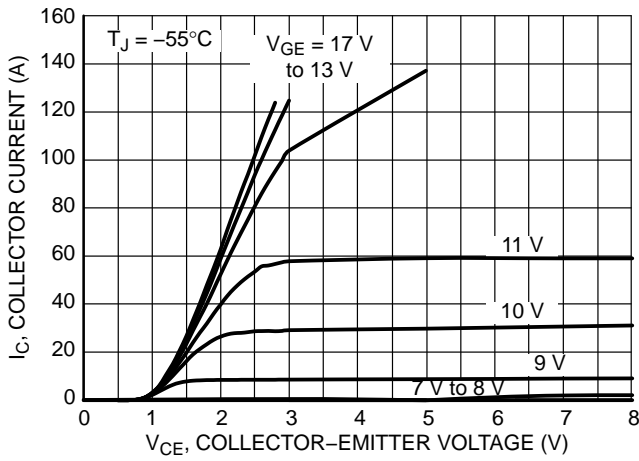


Figure 3. Output Characteristics

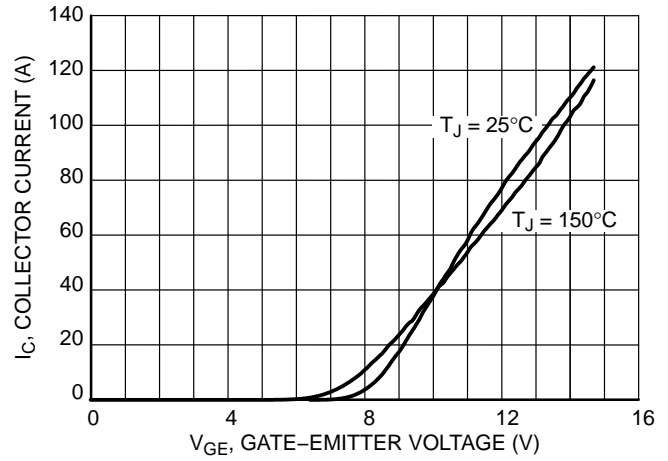


Figure 4. Typical Transfer Characteristics

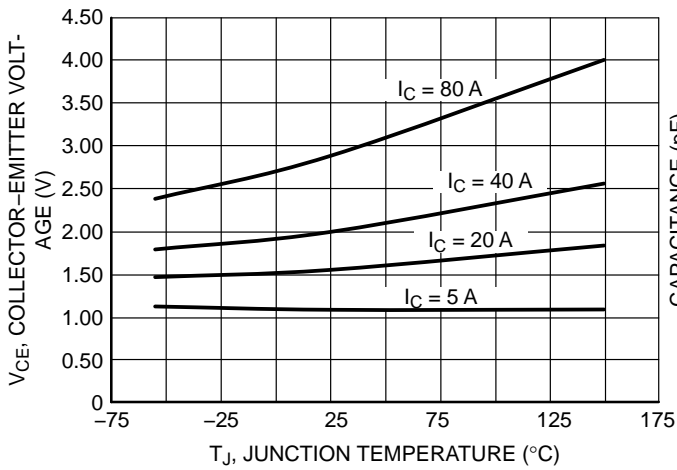


Figure 5. $V_{CE(sat)}$ vs. T_J

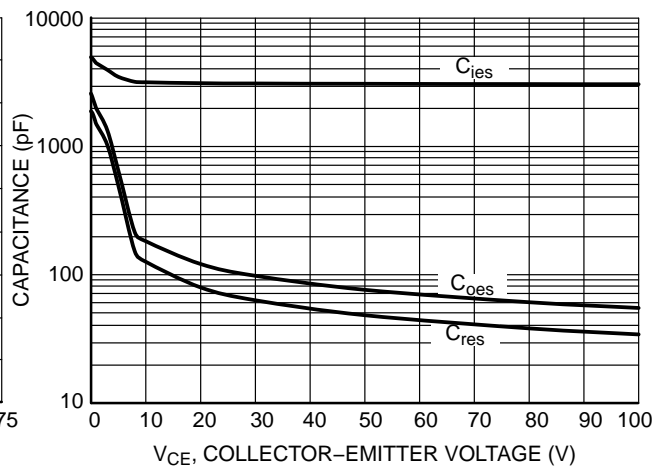


Figure 6. Typical Capacitance

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TYPICAL CHARACTERISTICS

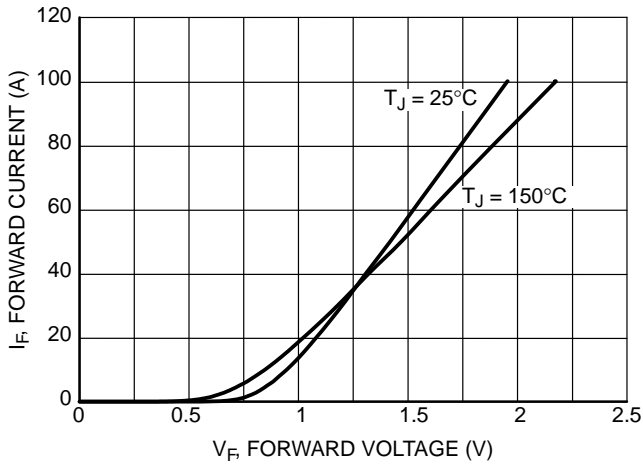


Figure 7. Diode Forward Characteristics

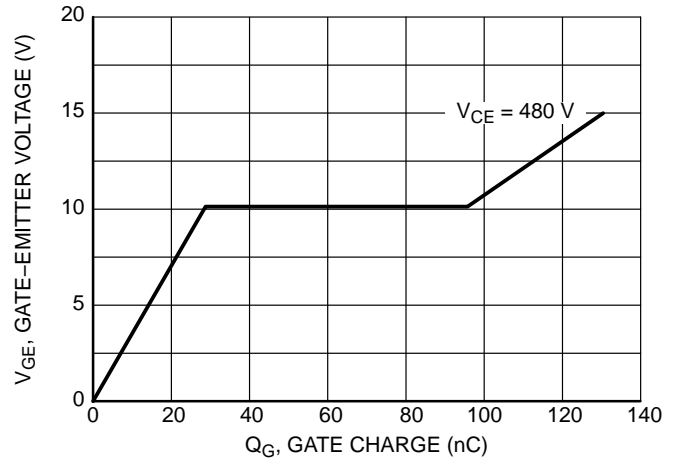


Figure 8. Typical Gate Charge

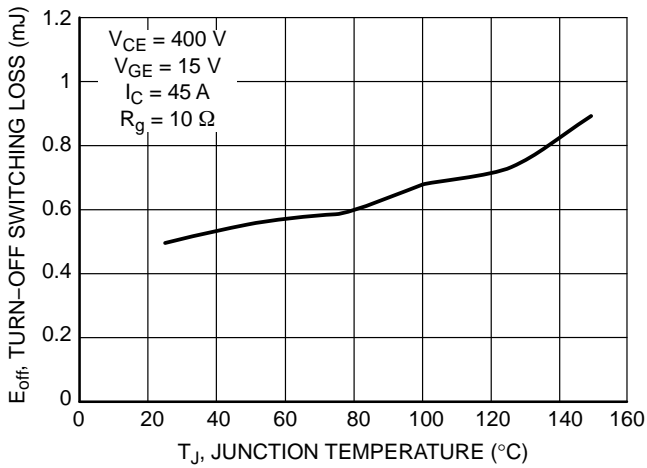


Figure 9. Switching Loss vs. Temperature

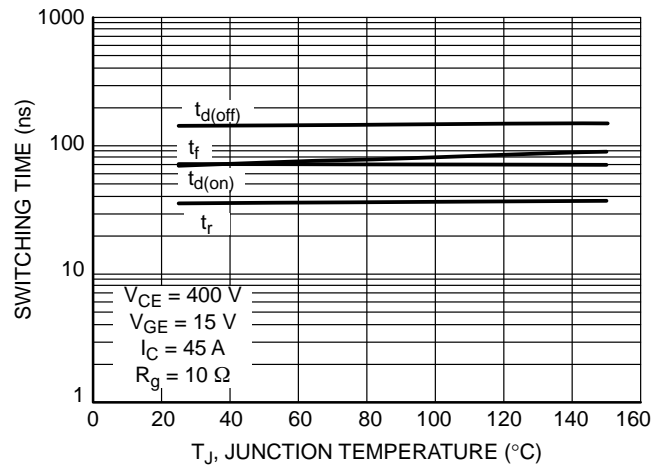


Figure 10. Switching Time vs. Temperature

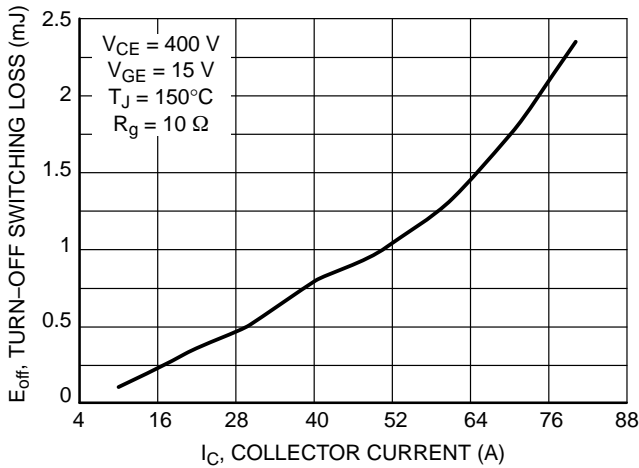


Figure 11. Switching Loss vs. I_C

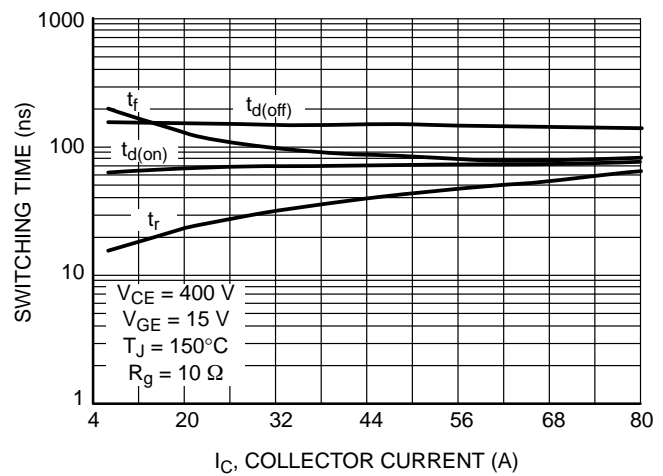
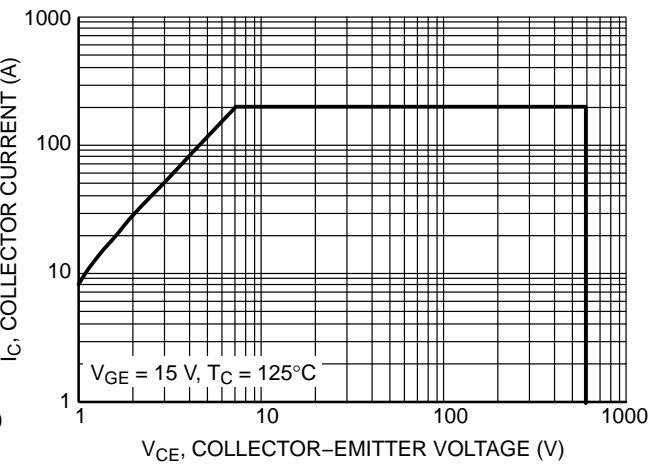
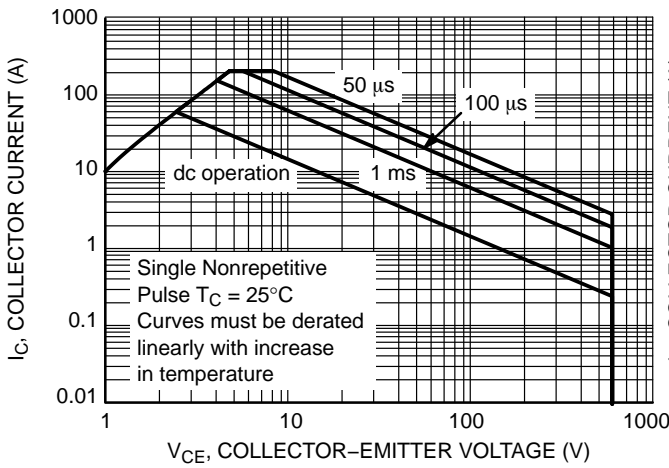
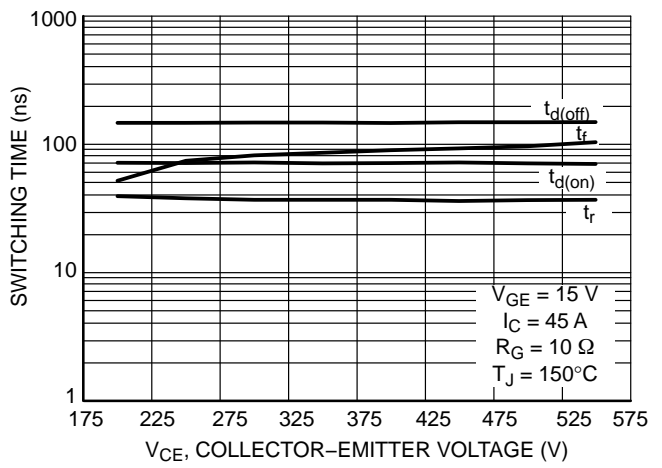
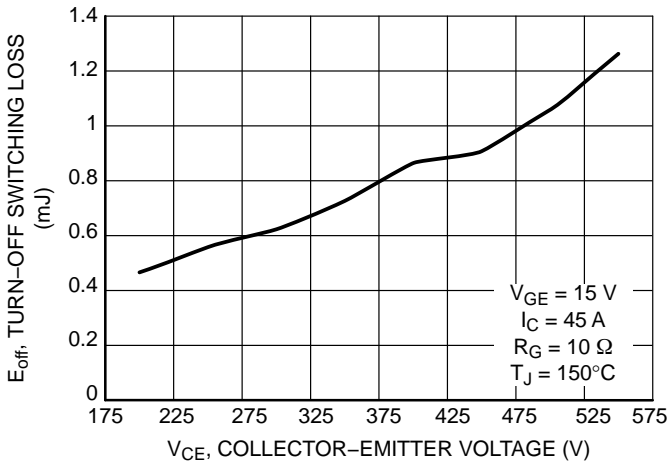
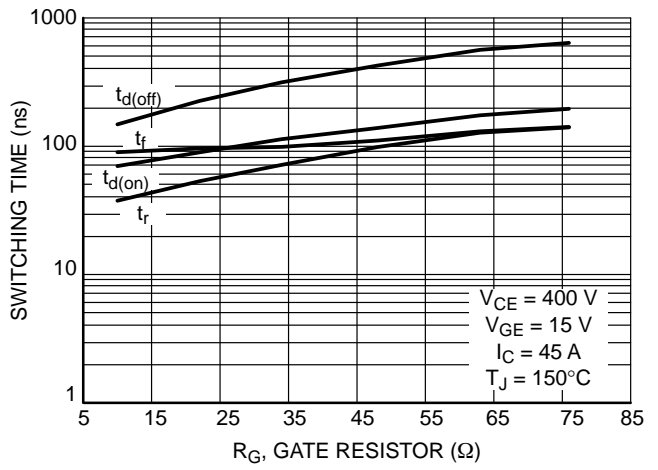
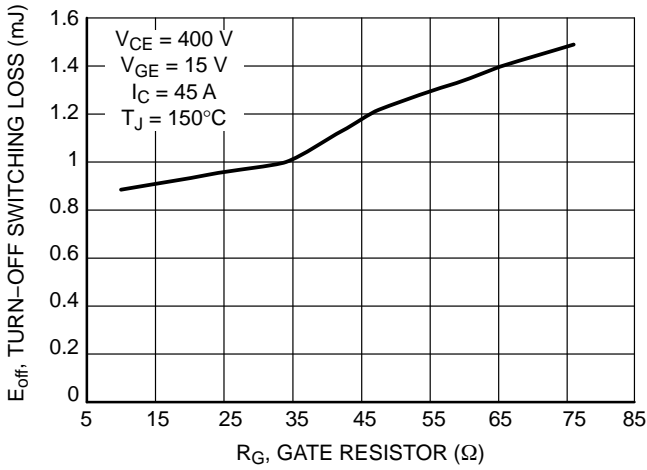


Figure 12. Switching Time vs. Current

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TYPICAL CHARACTERISTICS



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TYPICAL CHARACTERISTICS

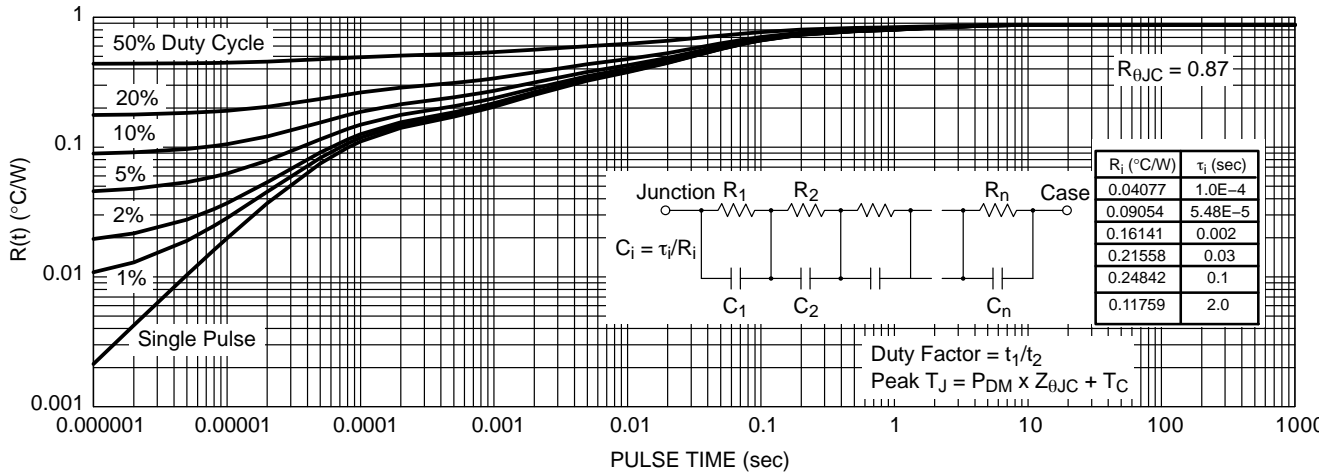


Figure 19. IGBT Transient Thermal Impedance

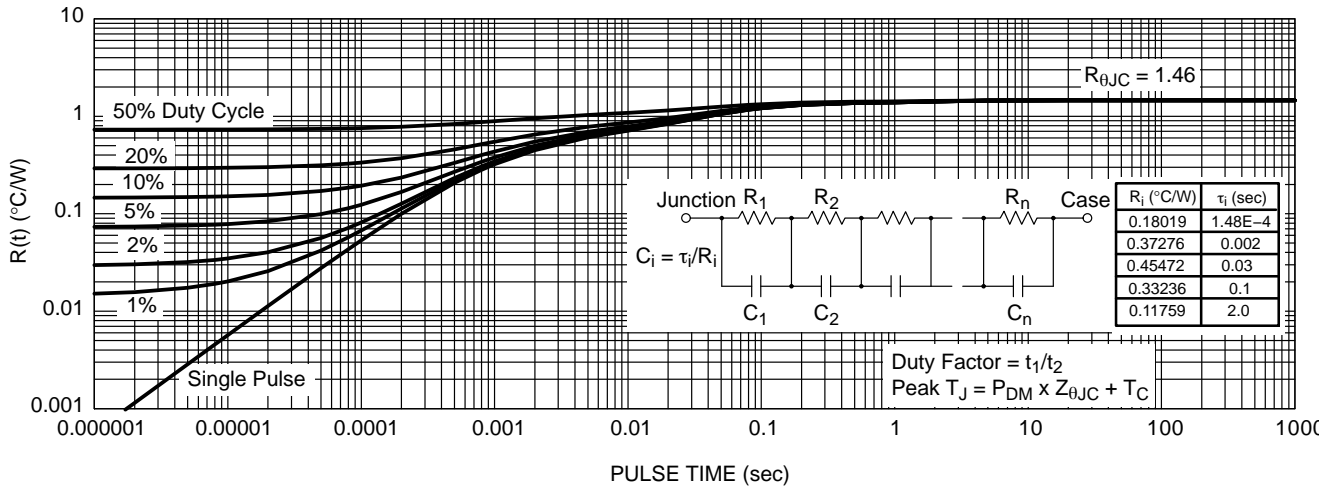


Figure 20. Diode Transient Thermal Impedance

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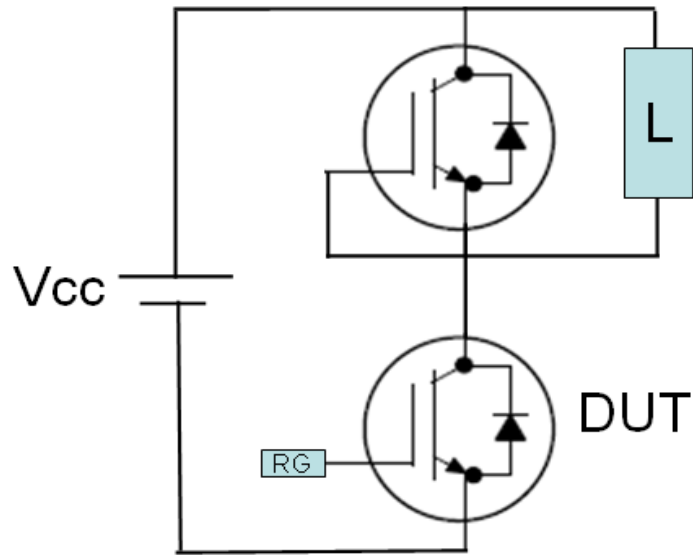


Figure 21. Test Circuit for Switching Characteristics

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Figure 22. Definition of Turn On Waveform

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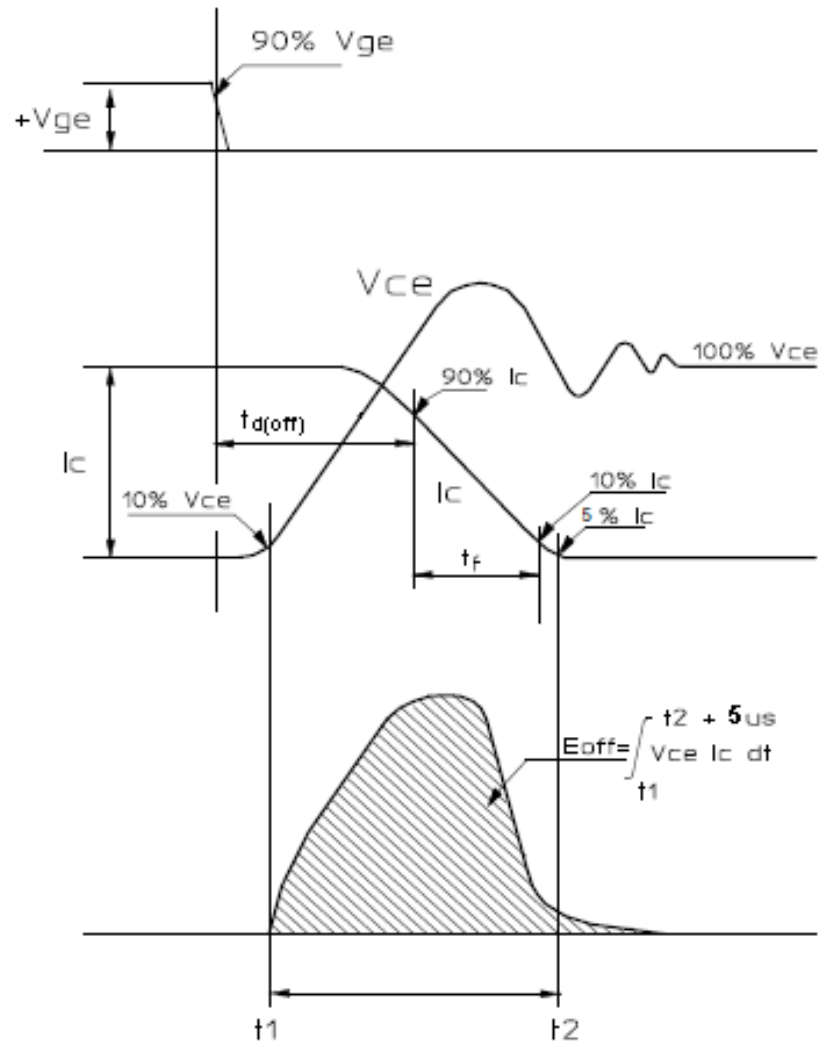
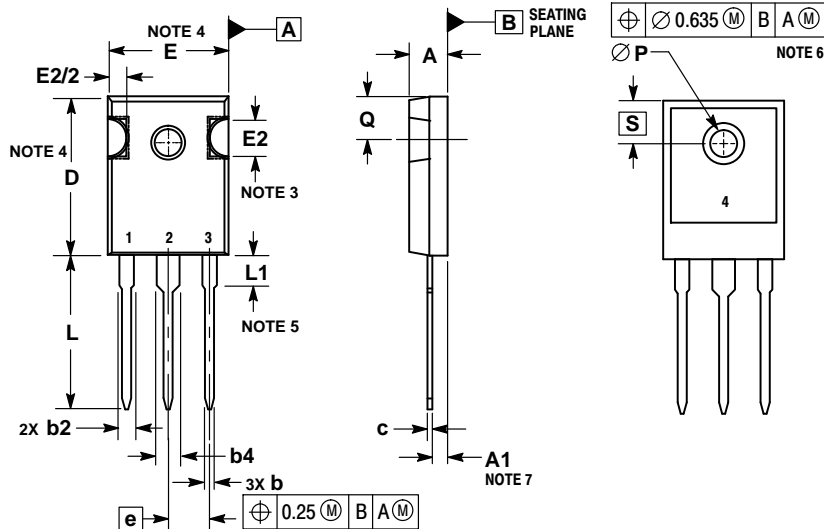


Figure 23. Definition of Turn Off Waveform

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PACKAGE DIMENSIONS

TO-247
CASE 340AL
ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. $\varnothing P$ SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS	
	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.00	1.40
b2	1.65	2.35
b4	2.60	3.40
c	0.40	0.80
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

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